

MOSFETs Silicon N-channel MOS (U-MOSX-H)

TK7R2E15Q5

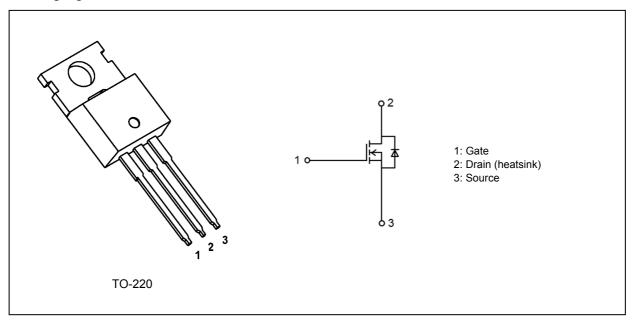
1. Applications

- High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) Fast reverse recovery time: t_{rr} = 44 ns (typ.)
- (2) Small reverse recovery charge : $Q_{rr} = 42 \text{ nC (typ.)}$
- (3) Small gate charge: $Q_{SW} = 20 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 6 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A (max) (V_{DS} = 150 V)$
- (6) Enhancement mode: $V_{th} = 3.1$ to 4.5 V ($V_{DS} = 10$ V, $I_D = 1.4$ mA)

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V_{DSS}	150	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	84	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I_D	130	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	330	
Power dissipation	(T _c = 25 °C)		P_D	230	W
Single-pulse avalanche energy		(Note 3)	E _{AS}	55	mJ
Single-pulse avalanche current		(Note 3)	I _{AS}	84	Α
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	°C
Mounting torque			TOR	0.6	N·m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance (T _c = 25 °C)	R _{th(ch-c)}	0.64	°C/W
Channel-to-ambient thermal resistance (T _a = 25 °C)	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited by silicon chip capability.

Note 3: V_{DD} = 100 V, T_{ch} = 25 °C (initial), L = 7.6 μ H, I_{AS} = 84 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	150			V
Drain-source breakdown voltage (Note 4)	V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	130	_		
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1.4 mA	3.1	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = 8 \text{ V}, I_D = 25 \text{ A}$	_	6.4	8.7	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 42 \text{ A}$		6	7.2	

Note 4: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz	_	4970	_	pF
Reverse transfer capacitance	C _{rss}		_	32	_	
Output capacitance	C _{oss}		_	1030	_	
Gate resistance	r _g	_	_	1.7	2.6	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	66	_	ns
Switching time (turn-on time)	t _{on}		_	96	_	
Switching time (fall time)	t _f		_	66	_	
Switching time (turn-off time)	t _{off}		_	110	_	

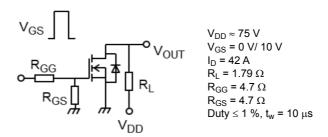


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 42 \text{ A}$	_	66	_	nC
gate-drain)		$V_{DD} \approx 75 \text{ V}, V_{GS} = 8 \text{ V}, I_D = 25 \text{ A}$	_	54	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 42 \text{ A}$	_	30	_	
Gate-drain charge	Q_{gd}		_	9.6	_	
Gate switch charge	Q_{SW}		_	20	_	
Output charge	Q _{oss}	V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz	_	127	_	



6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 5)	I _{DRP} (t = 100 μs)	_	-	_	330	Α
Diode forward voltage		V_{DSF}	I _{DR} = 42 A, V _{GS} = 0 V			-1.2	V
Reverse recovery time	(Note 6)	t _{rr}	I _{DR} = 21 A, V _{GS} = 0 V,	_	44	66	ns
Reverse recovery charge	(Note 6)	Q _{rr}	-dI _{DR} /dt = 100 A/μs		42	96	nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.

Note 6: Defined by design.

7. Marking

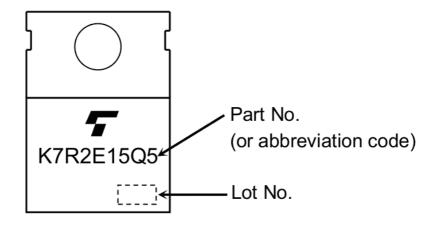


Fig. 7.1 Marking



8. Characteristics Curves (Note)

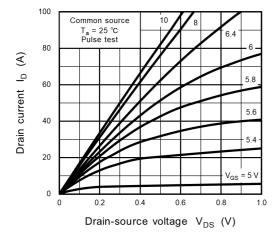


Fig. 8.1 I_D - V_{DS}

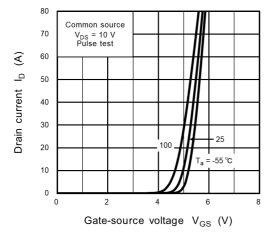


Fig. 8.3 I_D - V_{GS}

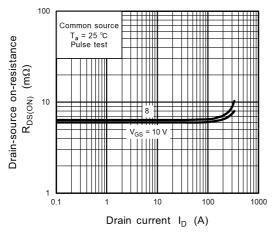


Fig. 8.5 R_{DS(ON)} - I_D

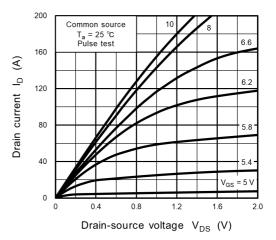


Fig. 8.2 I_D - V_{DS}

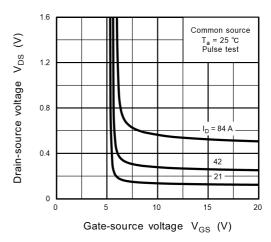


Fig. 8.4 V_{DS} - V_{GS}

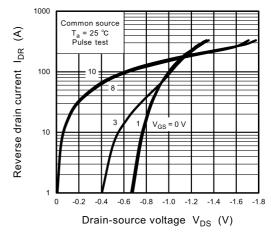


Fig. 8.6 IDR - VDS



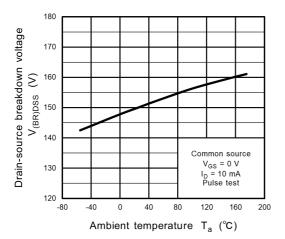


Fig. 8.7 V_{(BR)DSS} - T_a

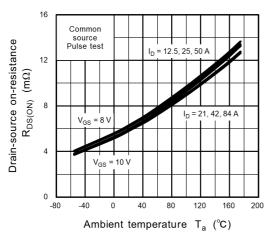


Fig. 8.9 R_{DS(ON)} - T_a

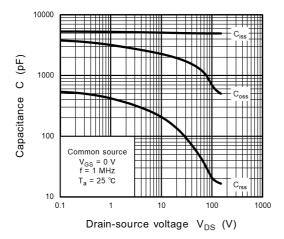


Fig. 8.11 Capacitance - V_{DS}

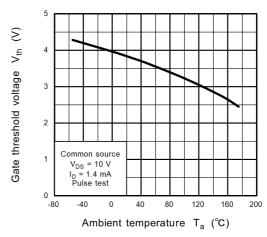


Fig. 8.8 V_{th} - T_a

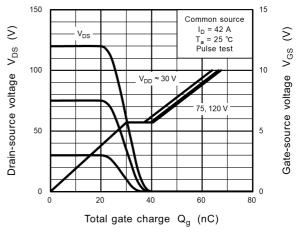


Fig. 8.10 Dynamic Input/Output Characteristics

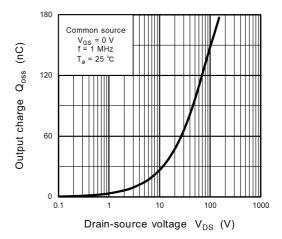


Fig. 8.12 Q_{oss} - V_{DS}



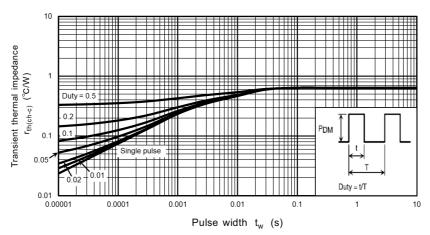
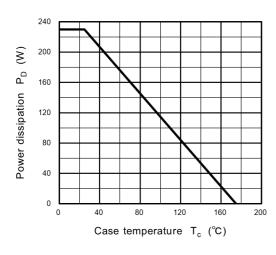


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)



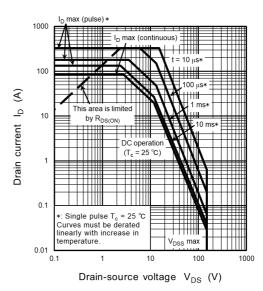


Fig. 8.14 P_D - T_c (Guaranteed Maximum)

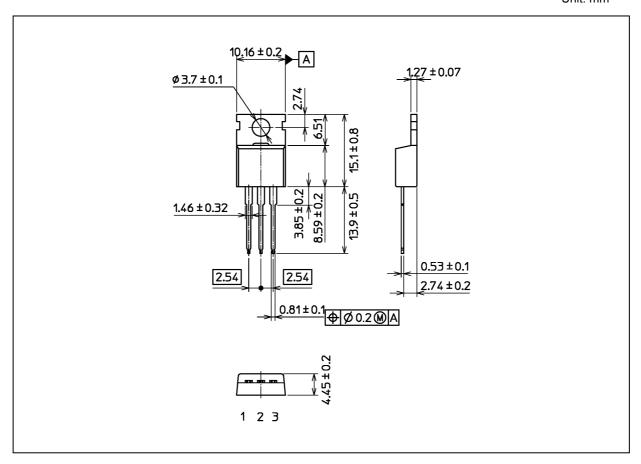
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.96 g (typ.)

Package Name(s)	
TOSHIBA: 2-10X1A	
Nickname: TO-220	



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